

LET19060C

RF POWER TRANSISTORS Ldmos Enhanced Technology

TARGET DATA

N-CHANNEL ENHANCEMENT-MODE LATERAL MOSFETs

• IS-97 CDMA PERFORMANCES

 $P_{OUT} = 7.5 \text{ W}$ EFF. = 18 %

• EDGE PERFORMANCES

 $P_{OUT} = 30 \text{ W}$ EFF. = 25 %

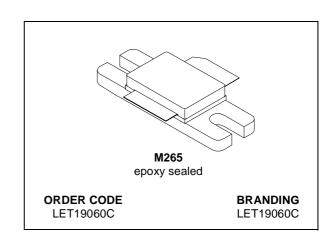
• GSM PERFORMANCES

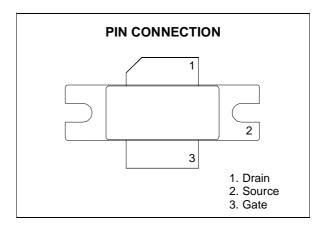
P_{OUT} = 65 W EFF. = 45 %

- EXCELLENT THERMAL STABILITY
- BeO FREE PACKAGE
- INTERNAL INPUT/OUTPUT MATCHING
- ESD PROTECTION



The LET19060C is a common source N-Channel enhancement-mode lateral Field-Effect RF power transistor designed for broadband commercial and industrial applications at frequencies up to 1.0 GHz. The LET19060C is designed for high gain and broadband performance operating in common source mode at 26 V. Its internal matching makes it ideal for base station applications requiring high linearity.





ABSOLUTE MAXIMUM RATINGS (T_{CASE} = 25 °C)

Symbol	Parameter	Value	Unit
V _{(BR)DSS}	Drain-Source Voltage	65	V
V _{GS}	Gate-Source Voltage	-0.5 to +15	V
I _D	Drain Current	7	Α
P _{DISS}	Power Dissipation (@ Tc = 70 °C)	130	W
Tj	Max. Operating Junction Temperature	200	°C
T _{STG}	Storage Temperature	-65 to +150	°C

THERMAL DATA

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	$R_{th(j-c)}$	Junction -Case Thermal Resistance	1.0	°C/W

ELECTRICAL SPECIFICATION (T_{CASE} = 25 °C)

STATIC (Per Section)

Symbol	Test Conditions	Min.	Тур.	Max.	Unit
V _{(BR)DSS}	$V_{GS} = 0 \text{ V}$ $I_D = 10 \mu\text{A}$	65			V
I _{DSS}	V _{GS} = 0 V V _{DS} = 26 V			6	μΑ
I _{GSS}	V _{GS} = 5 V V _{DS} = 0 V			1	μА
V _{GS(Q)}	V _{DS} = 26 V I _D = TBD	2.5		4.5	V
V _{DS(ON)}	V _{GS} = 10 V I _D = 2 A		0.27		V
G _{FS}	V _{DS} = 10 V I _D = 2 A		4.7		mho
C _{ISS} *	V _{GS} = 0 V V _{DS} = 26 V f = 1 MHz		TBD		pF
C _{OSS} *	V _{GS} = 0 V V _{DS} = 26 V f = 1 MHz		TBD		pF
C _{RSS}	V _{GS} = 0 V V _{DS} = 26 V f = 1 MHz		TBD		pF

^{*} Includes Internal Matching

Symbol	Test Conditions	Min.	Тур.	Max.	Unit
DYNAMIC (f =	2000 MHz)				
P _{1dB}	$V_{DD} = 26 \text{ V} I_{DQ} = \text{TBD}$	70	75		W
$\eta_D^{(1)}$	$V_{DD} = 26 \text{ V} I_{DQ} = \text{TBD}$	45	50		%
Load mismatch	V _{DD} = 26 V I _{DQ} = TBD P _{OUT} = 60 W ALL PHASE ANGLES			10:1	VSWR
DYNAMIC (f =	1930 - 1990 MHz)				
P _{1dB}	$V_{DD} = 26 \text{ V}$ $I_{DQ} = TBD$	60	65		W
G _P	$V_{DD} = 26 \text{ V}$ $I_{DQ} = TBD$ $P_{OUT} = 60 \text{ W}$	11	13		dB
$\eta_D^{(1)}$	$V_{DD} = 26 \text{ V} I_{DQ} = \text{TBD}$	40	45		%
Pout(CDMA) ⁽²⁾	885 KHz < -47 dBc 1.25 MHz < -55 dBc 2.25 MHz < -55 dBc		7.5		W
η _{D(CDMA)} ⁽²⁾	885 KHz < -47 dBc 1.25 MHz < -55 dBc 2.25 MHz < -55 dBc		18		%
DYNAMIC (f =	1805 - 1880 MHz)				
P _{1dB}	$V_{DD} = 26 \text{ V} I_{DQ} = \text{TBD}$	60	65		W
G_P	$V_{DD} = 26 \text{ V}$ $I_{DQ} = TBD$ $P_{OUT} = 60 \text{ W}$	11	13		dB
$\eta_D^{(1)}$	V _{DD} = 26 V I _{DQ} = TBD	45			%
P _{OUT(EDGE)}	400 KHz < -60 dBc 600 KHz < -70 dBc EVM < 3 %		30		W
η _{D(EDGE)}	400 KHz < -60 dBc 600 KHz < -70 dBc EVM < 3 %		25		%

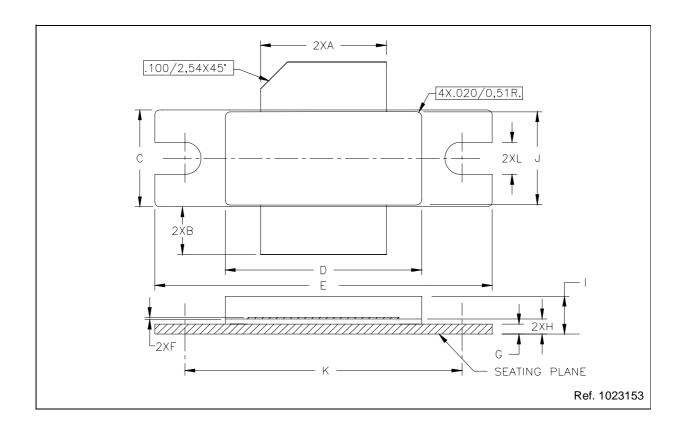
^{(1) 1} dB Compression point (2) IS-97 CDMA Pilot, Sync, Paging, Traffic, Codes 8 Thru 13

ESD PROTECTION CHARACTERISTICS

Test Conditions	Class
Human Body Model	2
Machine Model	M3

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DIM		mm			Inch	
DIM.	MIN.	TYP.	MAX	MIN.	TYP.	MAX
А	12.57		12.83	.495		.505
В	4.32		5.33	.170		.210
С	9.65		9.91	.380		.390
D	19.61		20.02	.772		.788
E	33.91		34.16	1.335		1.345
F	0.08		0.15	.003		.006
G	0.89		1.14	.035		.045
Н	1.45		1.70	.057		.067
I	3.18		4.32	.125		.170
J	9.27		9.53	.365		.375
K	27.69		28.19	1.090		1.110
L	3.00		3.51	.118		.138



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